

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A semiconductor device having a gate electrode ~~7b~~ formed on a silicon substrate ~~1~~ through via a gate insulating film is ~~constituted~~ formed by laminating the gate insulating film with a silicon oxide film ~~4a~~, formed on the silicon substrate ~~1~~, an Hf silicate film ~~5a~~ is formed on the silicon oxide film ~~4a~~, and a nitrogen-containing Hf silicate film ~~6a~~ formed on the Hf silicate film ~~5a~~, and containing Hf in a peak concentration ~~of 1~~ in a range from one atomic % or more and ~~30~~ to thirty atomic % or less, and nitrogen in a peak concentration ~~of 10~~ in a range from ten atomic % or more and ~~30~~ to thirty atomic % or less.